(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
22 July 2004 (22.07.2004)

PCT

(10) International Publication Number
WO 2004/061969 A1

(51) International Patent Classification[7]: H01L 29/22, 51/40

(21) International Application Number: PCT/US2003/021916

(22) International Filing Date: 15 July 2003 (15.07.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
60/433,844 16 December 2002 (16.12.2002) US
60/433,843 16 December 2002 (16.12.2002) US

(71) Applicant *(for all designated States except US)*: **THE REGENTS OF UNIVERSITY OF CALIFORNIA** [US/US]; 1111 Franklin Street, 12th Floor, Oakland, CA 94607 (US).

(72) Inventors; and

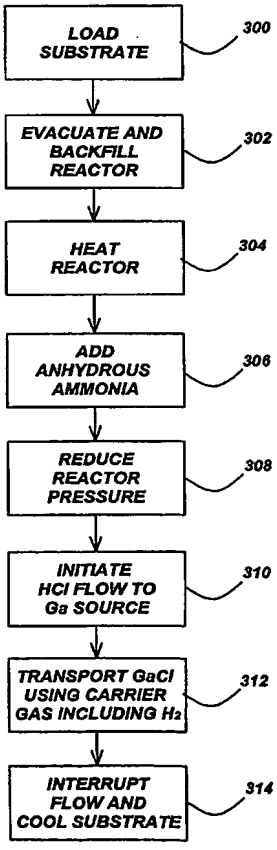
(75) Inventors/Applicants *(for US only)*: **HASKELL, Benjamin, A.** [US/US]; 724 Kroeber Walk, #207, Goleta, CA 93117 (US). **FINI, Paul, T.** [US/US]; 218 West Mason Street, Santa Barbara, CA 93101 (US). **MATSUDA, Shigemasa** [JP/JP]; 3-19-1-212 Hyakunin-cho, Shinjuku-ku, Tokyo 169-0073 (JP). **CRAVEN, Michael, D.** [US/US]; 68 1/2 Deerhurst Drive, Goleta,CA 93117 (US). **DENBAARS, Steven, P.** [US/US]; 287 King Daniel Lane, Goleta, CA 93117 (US). **SPECK, Jame, S.** [US/US]; 947 West Campus Lane, Goleta, CA 93117 (US). **NAKAMURA, Shuji** [JP/US]; 4517 Vieja Drive, Santa Barbara, CA 93110 (US).

(74) Agent: **GATES, George, H.**; Gates & Cooper LLP, 6701 Center Drive West, Suite 1050, Los Angeles, CA 90045 (US).

(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH,

[Continued on next page]

(54) Title: GROWTH OF PLANAR, NON-POLAR A-PLANE GALLIUM NITRIDE BY HYDRIDE VAPOR PHASE EPITAXY



(57) Abstract: Highly planar non-polar a-plane GaN films are grown by hydride vapor phase epitaxy (HVPE). The resulting films are suitable for subsequent device regrowth by a variety of growth techniques

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